

NUP1301ML3T1G, SZNUP1301ML3T1G

MAXIMUM RATINGS (Each Diode) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------------|-------------------|------|
| Reverse Voltage | V_R | 70 | Vdc |
| Forward Current | I_F | 215 | mAdc |
| Peak Forward Surge Current | $I_{FM(surge)}$ | 500 | mAdc |
| Repetitive Peak Reverse Voltage | V_{RRM} | 70 | V |
| Average Rectified Forward Current (Note 1) (averaged over any 20 ms period) | $I_{F(AV)}$ | 715 | mA |
| Repetitive Peak Forward Current | I_{FRM} | 450 | mA |
| Non-Repetitive Peak Forward Current $t = 1.0 \mu\text{s}$ $t = 1.0 \text{ms}$ $t = 1.0 \text{S}$ | I_{FSM} | 2.0 1.0 0.5 | A |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|---------------------------|
| Thermal Resistance Junction-to-Ambient | $R_{\theta JA}$ | 625 | $^\circ\text{C}/\text{W}$ |
| Lead Solder Temperature Maximum 10 Seconds Duration | T_L | 260 | $^\circ\text{C}$ |
| Junction Temperature | T_J | -65 to 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|------------|-----|-----|----------------------------|------------------|
| OFF CHARACTERISTICS | | | | | |
| Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$) | $V_{(BR)}$ | 70 | - | - | Vdc |
| Reverse Voltage Leakage Current ($V_R = 70 \text{Vdc}$) ($V_R = 25 \text{Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{Vdc}$, $T_J = 150^\circ\text{C}$) | I_R | - | - | 2.5 30 50 | μAdc |
| Diode Capacitance (between I/O and ground) ($V_R = 0$, $f = 1.0 \text{MHz}$) | C_D | - | - | 0.9 | pF |
| Forward Voltage ($I_F = 1.0 \text{mAdc}$) ($I_F = 10 \text{mAdc}$) ($I_F = 50 \text{mAdc}$) ($I_F = 150 \text{mAdc}$) | V_F | - | - | 715 855 1000 1250 | mV_{dc} |

2. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

3. Alumina = $0.4 \times 0.3 \times 0.024$ in, 99.5% alumina.

4. Include SZ-prefix devices where applicable.

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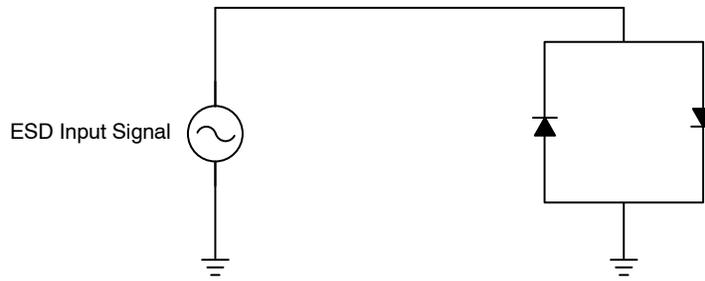


Figure 1. ESD Test Circuit

APPLICATION NOTE

Electrostatic Discharge

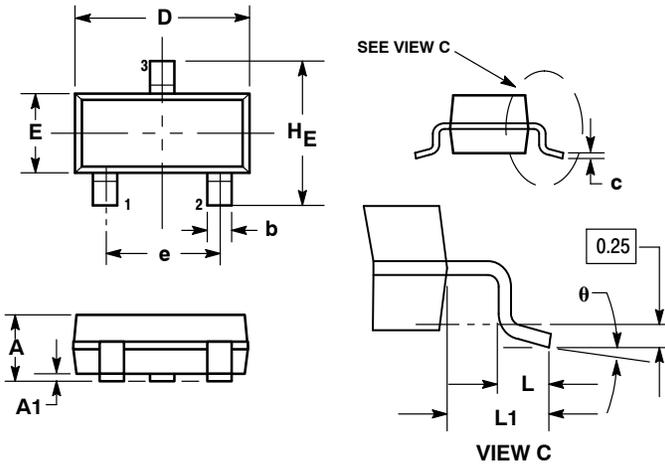
A common means of protecting high-speed data lines is to employ low-capacitance diode arrays in a rail-to-rail configuration. Two devices per line are connected between two fixed voltage references such as V_{CC} and ground. When the transient voltage exceeds the forward voltage (V_F) drop of the diode plus the reference voltage, the diodes direct the

surge to the supply rail or ground. This method has several advantages including low loading capacitance, fast response time, and inherent bidirectionality (within the reference voltages). See Figure 1 for the test circuit used to verify the ESD rating for this device.

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

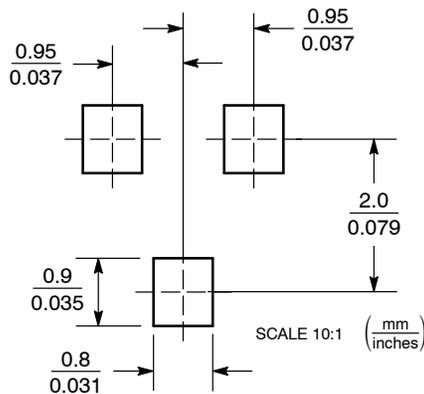
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.040 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.018 | 0.020 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.081 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| θ | 0° | --- | 10° | 0° | --- | 10° |

STYLE 11:

1. ANODE
2. CATHODE
3. CATHODE-ANODE

SOLDERING FOOTPRINT



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